

RF Modeling and Characterization at TSMC using Integrand's EMX

Dr. Sharad Kapur, President
Integrand Software, Inc.

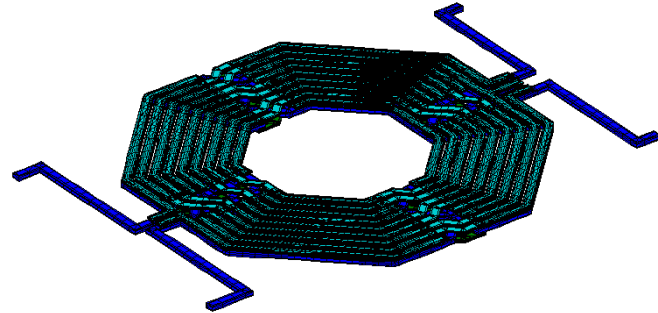
- EMX is a full-wave 3D EM simulation tool
 - Used by TSMC for generation of PDK models
 - Uses TSMC's new iRCX technology file
 - Can be used from within PDK directly
 - RF Reference Design Kit 2.0 for 65nm (VCO)
- Used by several TSMC customers for RFIC and high-speed design

EMX 3D EM simulator

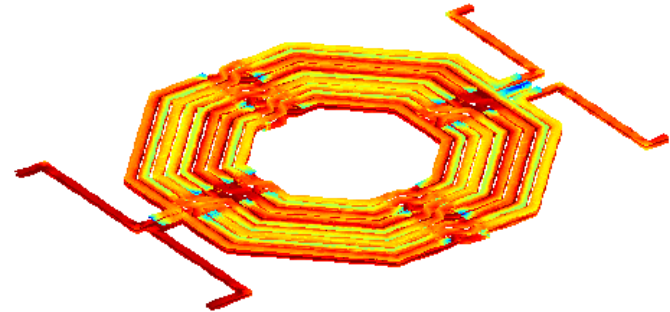
- All physical effects included
 - R, L, C, substrate in a fully coupled manner (solving Maxwell's equations)

$$E_s(r) = \frac{1}{\sigma} J(r) + j\omega A(r) + \nabla \phi(r).$$

- Inductance
 - Distributed 3D volume currents
- Resistance
 - Skin effect and volume loss
- Capacitance
 - Accurate side-wall capacitance
 - MIM and thin-film capacitors
- Substrate

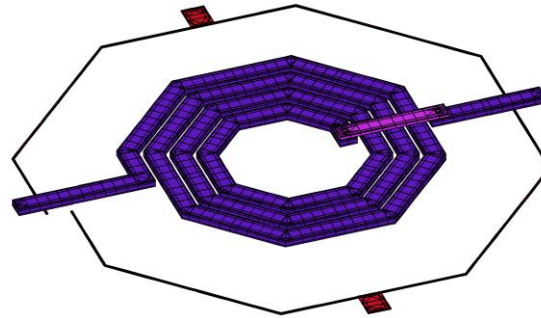


Mesh and current for balun

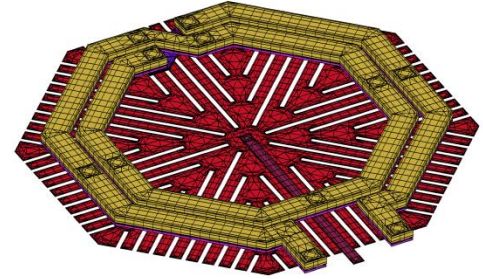


Passive Components

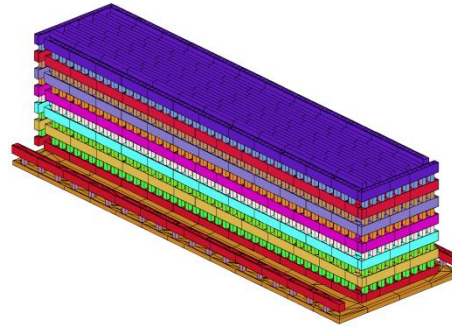
- 3D EM simulation of passive components
- Used for component characterization and scalable model generation for PDKs



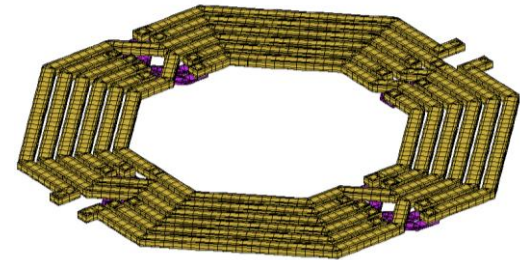
Inductor



Inductor with shield

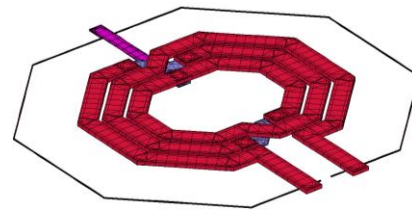


MOM capacitor

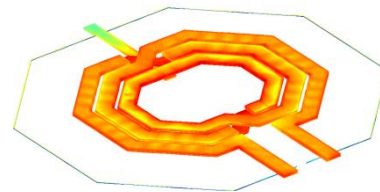


Transformer

- TSMC uses EMX for
 - Scalable models for PDKs
 - STD/SYM/Stacked inductors
 - RTMOM capacitors
- Verified for 180nm-28nm



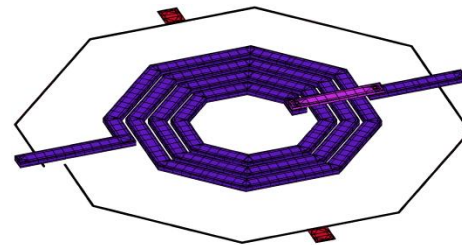
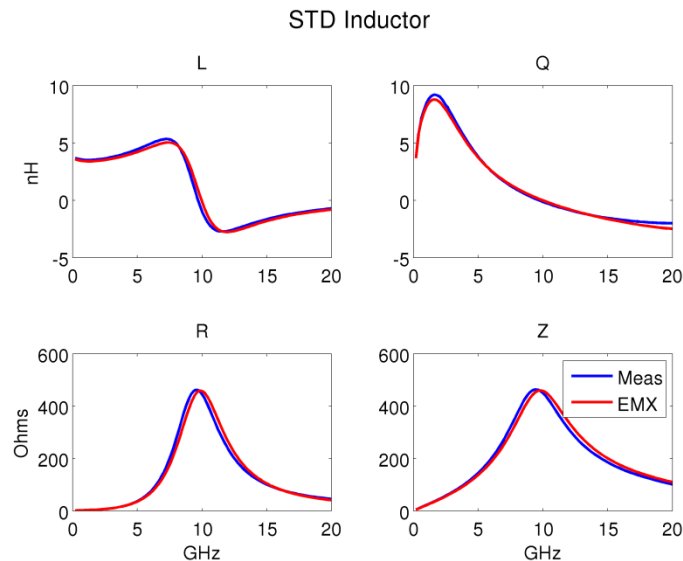
Mesh and current for inductor



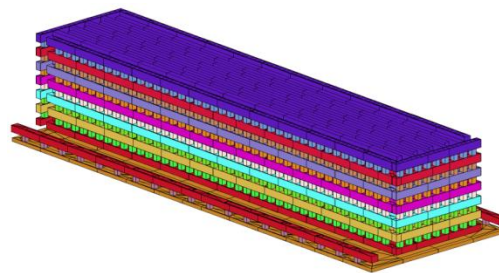
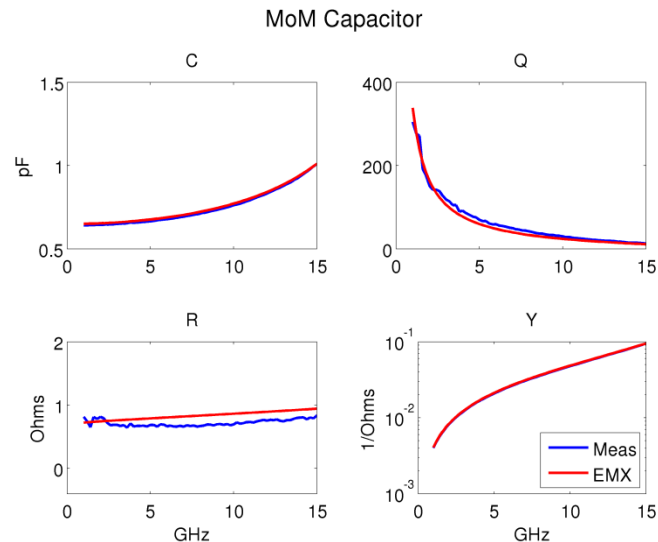
...Extensive verification...for a few generations of technologies, has demonstrated the accuracy and won our confidence in their tools....

- Dr. Sally Liu, Spice Modeling Department

- Very Accurate
 - 3D Conductors and Vias
 - True volume currents
 - Sidewall capacitance
 - Substrate effects
- TSMC uses EMX for
 - Inductor modeling
 - In PDK

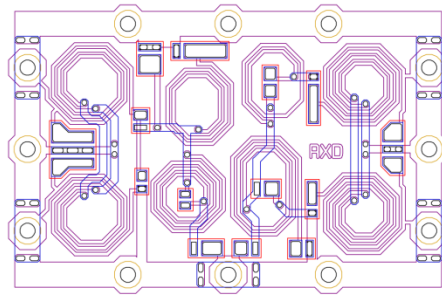


- Very Accurate
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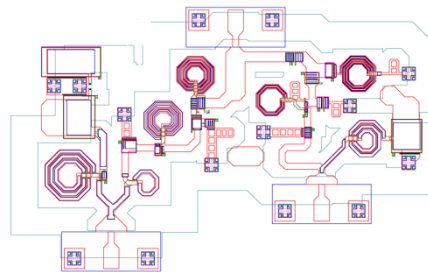


EMX for large circuits

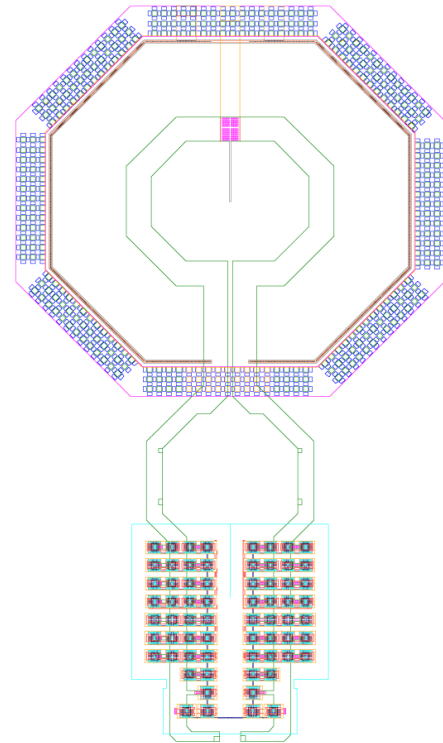
- 3D Full-wave EM simulation tool
- Applications
 - VCOs, LNAs
 - Diplexers



Diplexer



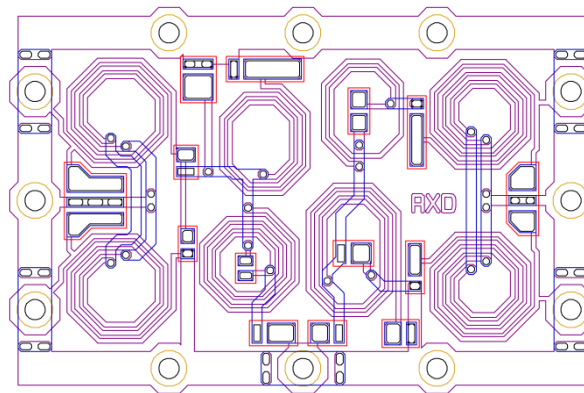
Full circuit



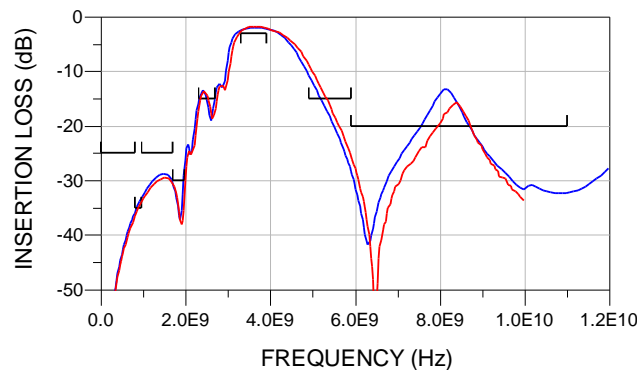
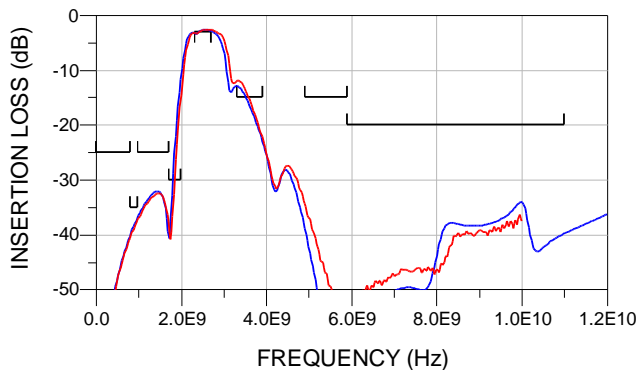
VCO

EMX distinguishing features

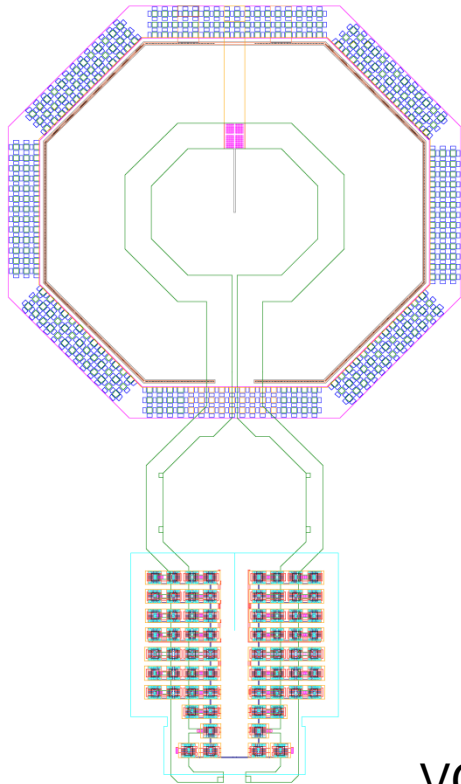
- Speed and capacity
 - 10-50X faster than other EM tools
 - **10X larger problems**



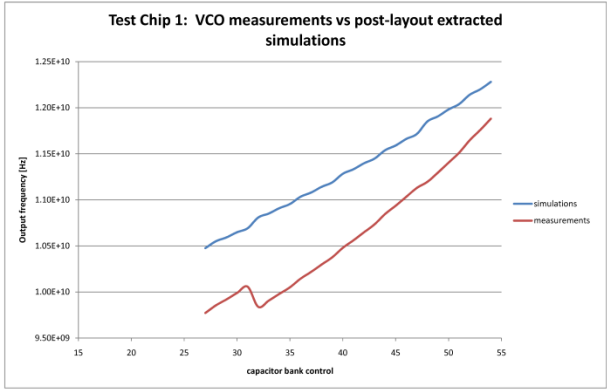
Dual Band WiMax Diplexer



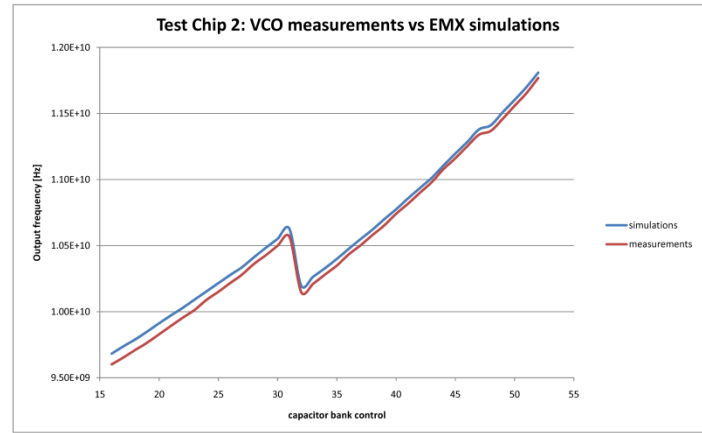
90nm VCO using iRCX



VCO

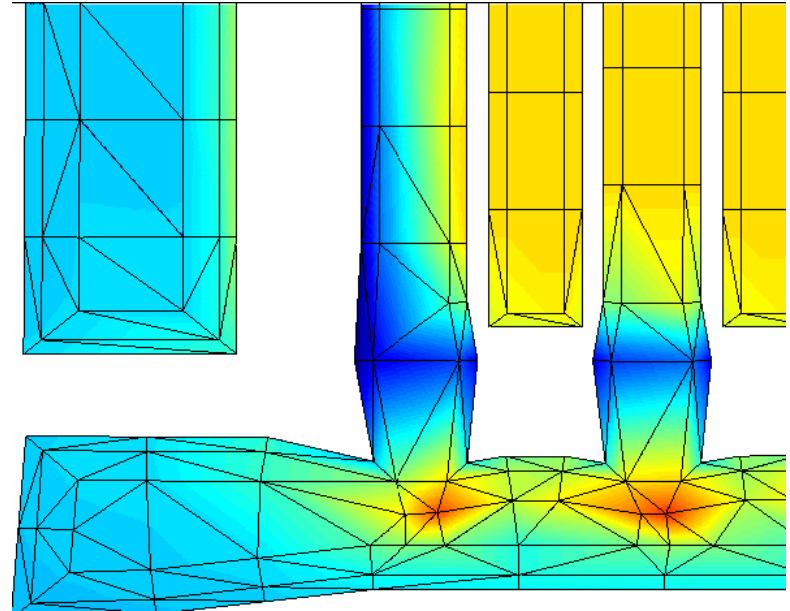


Before EMX

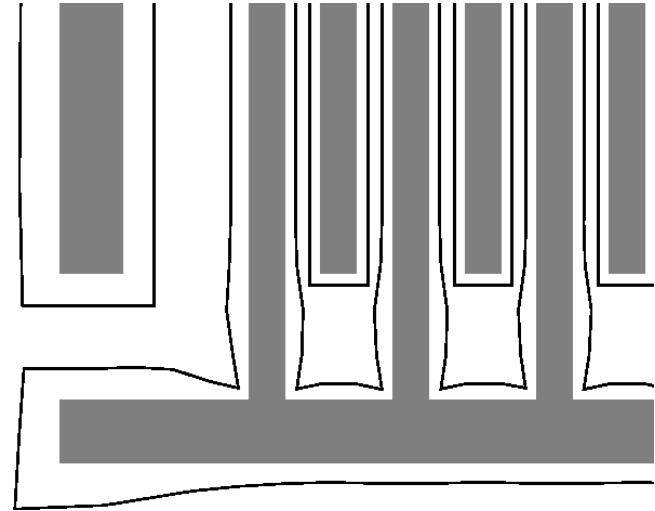


EMX+iRCX

- TSMC iRCX
 - Technology properties
 - Width/spacing dependence
 - Sheet resistance variation
 - Metal width and bias variation
 - Parser converts iRCX to EMX process file
 - Paper at RFIC 09



- Drawing vs Fabrication
 - EMX mimics actual fabrication



Drawn vs Fabricated Layout

...Several mutual customers that use EMX+iRCX and have achieved first pass silicon success....

- Dr. Pike Chang, PDK Department

TSMC Customers using iRCX+EMX

Integrand
Software, Inc.

MEDIA TEK

LSI

SILICON LABS

REALTEK

HUAWEI

MARVELL

Ralink

ST ERICSSON

JAVELIN SEMICONDUCTOR

WIPRO
Applying Thought

MARVELL

The iRCX flow with EMX is very useful to us...it has enabled us to achieve the best die size/performances of analog RF circuit and achieve first pass success at 55nm and 65nm nodes.– Dr. Cao Thong Tu, Design Manager, Marvell

WIPRO
Applying Thought

Since we have started using EMX+iRCX, high frequency design is no longer Russian Roulette– Dr. Carla Ghidini, Newlogic, Wipro

EMX design flow for RDK 2.0

Integrand
Software, Inc.

System to RFIC Specification Sign-off

Schematic Capture

Circuit Design and Pre-Layout Simulation

Block Layout DRC/LVS

RCLK Parasitic Extraction & Post-Layout Simulation

Block-Level Design

3D full-wave EM solver
tsmc iRCX support

Spiral & interconnect
Model generation

modified
LVS deck

EMX models

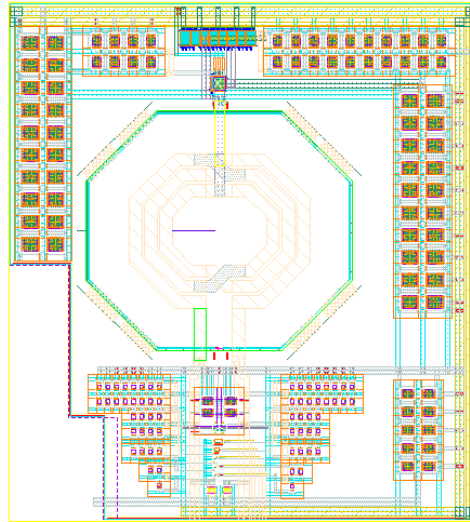
EMX

Black-box
flow
&
PDK
integration

Top-Level Closed-Loop Integration
& Verification

RF RDK 2.0 65nm VCO

- TSMC provides a RF Reference Design Kit (RF RDK 2.0) 65nm
- VCO design
- Pre and Post-layout simulation
- Excellent agreement with reference



65nm VCO

